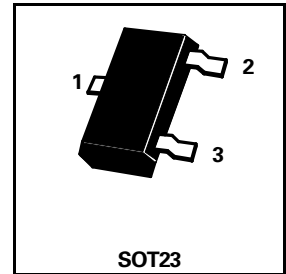
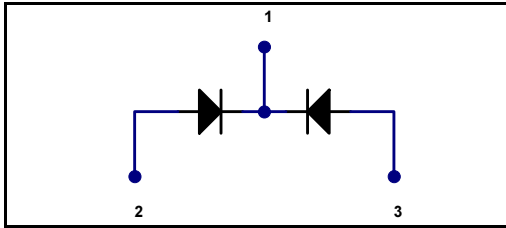


# SOT23 SILICON PLANAR LOW LEAKAGE COMMON CATHODE DIODE PAIR

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## FLLD258



PART MARKING DETAIL – D58

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current (t=1 $\mu$ s)	$I_{FSM}$	3.0	A
Power Dissipation at $T_{amb} = 25^{\circ}\text{C}$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	$I_R$		3 5	nA $\mu\text{A}$	$V_{RRM}=50\text{V}$ $V_{RRM}=100\text{V}, T_{amb}=150^{\circ}\text{C}$
Reverse Recovery Time*	$t_{rr}$		400	ns	$I_F = I_R = 50 - 400\text{mA}$
Forward Recovery Time	$t_{fr}$		10	ns	$I_F = 10\text{mA}$
Diode Capacitance	$C_d$		4	pF	$V_R = 1\text{V}, f = 1\text{MHz}$
Forward Overshoot Voltage	$V_{fr}$		Typ 0.9	V	$I_F = 10\text{mA}$ , Rise time = $5\text{ns} \pm 20\%$
Forward Voltage	$V_F$		1.4	V	$I_F = -200\text{mA}$

\*Time for  $I_R$  to recover to 10% of  $I_R$  peak  
For typical characteristics graphs see FLLD263 datasheet.

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**TYPICAL CHARACTERISTICS**

